650V Super-Junction Power MOSFET

DESCRIPTION

650V super-junction Power MOSFET

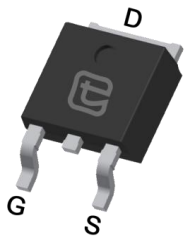
Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The SJ MOSFET is a price-performance optimized product enabling to target cost sensitive applications in Consumer and Lighting markets, designed by Wuxi Unigroup Microelectronics Company.

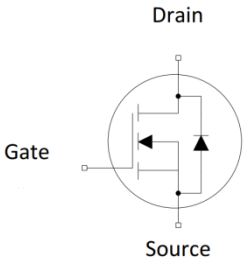
FEATURES

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)





RoHS

Device Marking and Package Information

Device	Package	Marking
TPD65R520D	TO-252	65R520D

Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	650	V
$R_{DS(on),max}$	0.52	Ω
I_D	7	A
$Q_{g,typ}$	12.5	nC
I_{DM}	21	A

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted				
Parameter		**Symbol**	**Value**	**Unit**
Drain-Source Voltage (V_{GS} = 0V)		V_{DSS}	650	V
Continuous Drain Current	T_C = 25ºC	I_D	7	A
	T_C = 100ºC		4	
Pulsed Drain Current (note1)		I_{DM}	21	A
Gate-Source Voltage		V_{GSS}	±30	V
Single Pulse Avalanche Energy (note2)		E_{AS}	45	mJ
Avalanche Current		I_{AS}	3	A
Power Dissipation		P_D	62.5	W
Continuous Body Diode Current		I_S	7	A
Pulsed Diode Forward Current (note1)		I_{SM}	21	
MOSFET dv/dt ruggedness, V_{DS} = 0...650V		dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS} = 0…650V, $I_{SD} \le I_D$		dv/dt	5	A/us
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150	ºC

Thermal Resistance			
Parameter	**Symbol**	**Value**	**Unit**
Thermal Resistance, Junction-to-Case	R_{thJC}	2	ºC/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	

Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 650V, V_{GS} = 0V, T_J = 25ºC	--	--	1	μA
		V_{DS} = 650V, V_{GS} = 0V, T_J = 150ºC	--	--	100	
Gate-Source Leakage	I_{GSS}	V_{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.5	--	4.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 3A	--	0.44	0.52	Ω
Forward Transconductance (Note3)	g_{fs}	V_{DS} = 20V, I_D = 3A	--	3.6	--	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 100V, f = 1.0MHz	--	564	--	pF
Output Capacitance	C_{oss}		--	22	--	
Reverse Transfer Capacitance	C_{rss}		--	0.5	--	
Total Gate Charge	Q_g	V_{DD} = 520V, I_D = 7A, V_{GS} = 10V	--	12.5	--	nC
Gate-Source Charge	Q_{gs}		--	5	--	
Gate-Drain Charge	Q_{gd}		--	3.2	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 400V, I_D = 7A, R_G = 25Ω	--	52	--	ns
Turn-on Rise Time	t_r		--	62	--	
Turn-off Delay Time	$t_{d(off)}$		--	84	--	
Turn-off Fall Time	t_f		--	50	--	
Drain-Source Body Diode Characteristics						
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 7A, V_{GS} = 0V	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R = 400V, I_S=3A, di_F/dt = 100A/μs	--	200	--	ns
Reverse Recovery Charge	Q_{rr}		--	1.6	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	3.2	--	A

Notes

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2. V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 1%

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

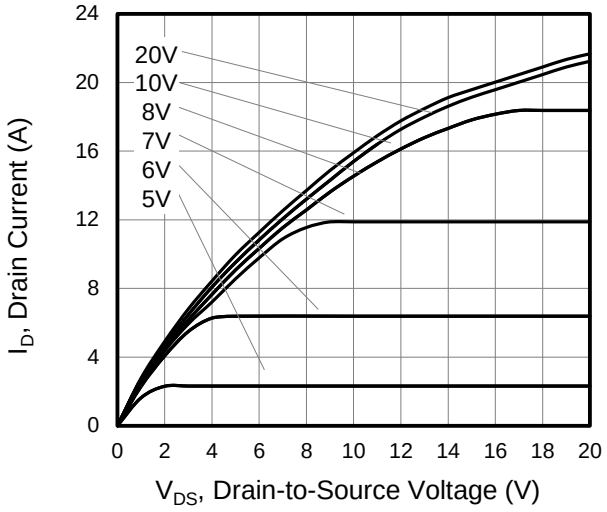


Figure 2. Transfer Characteristics

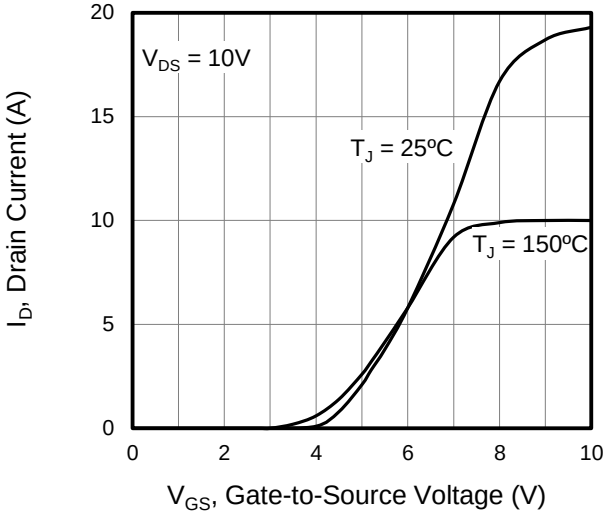


Figure 3 . Body Diode Forward Voltage

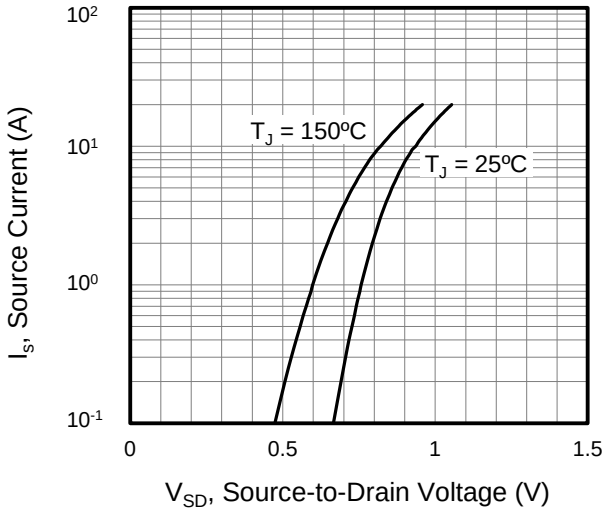


Figure 4. Capacitance

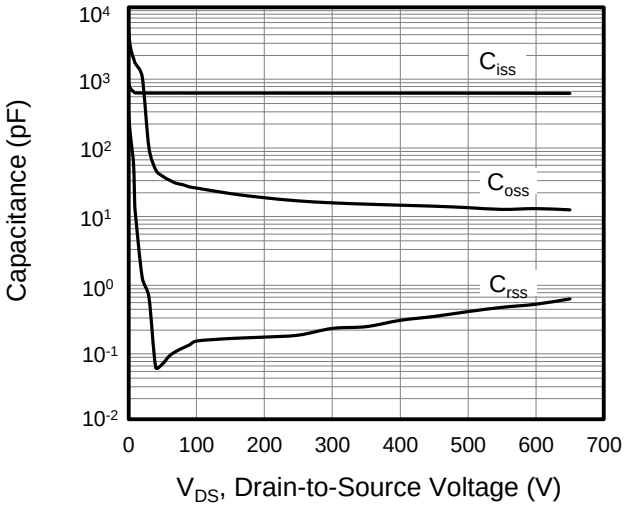


Figure 5. Gate Charge

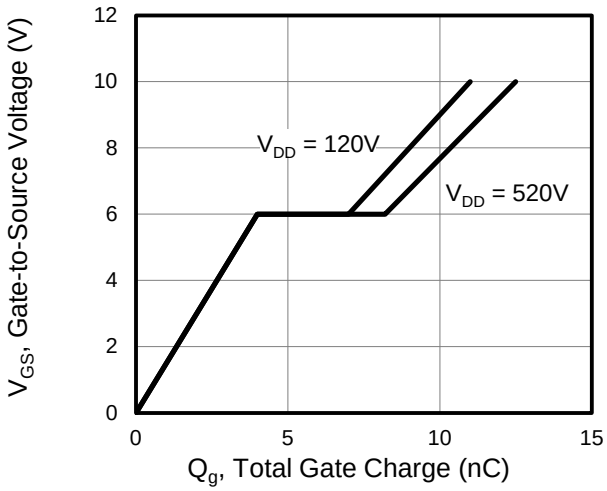


Figure 6. On-Resistance vs.Junction Temperature

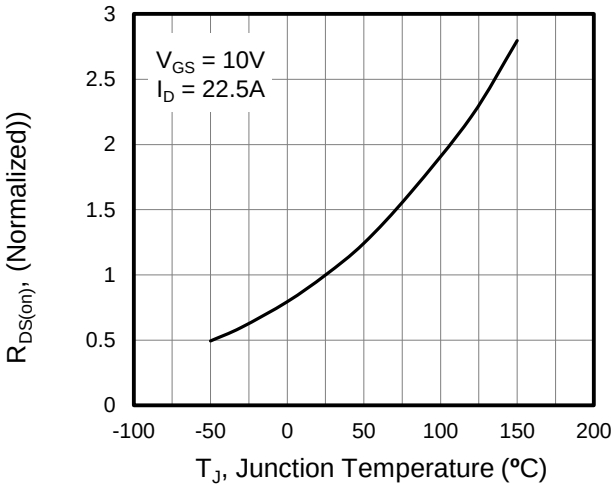


Figure 7. Breakdown voltage vs. Junction Temperature

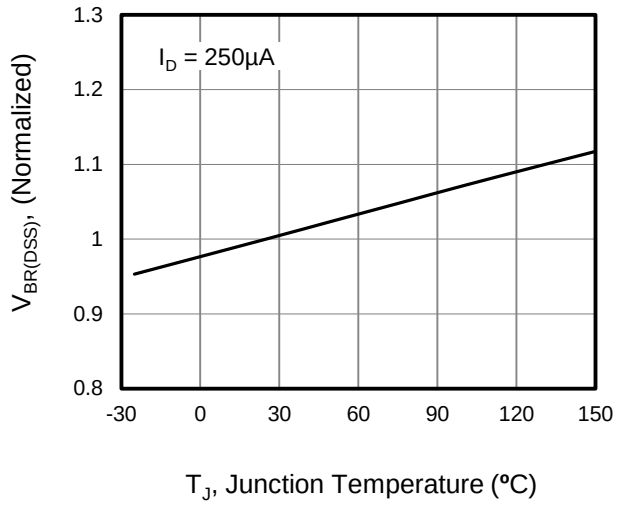


Figure 8. Threshold Voltage vs. Junction Temperature

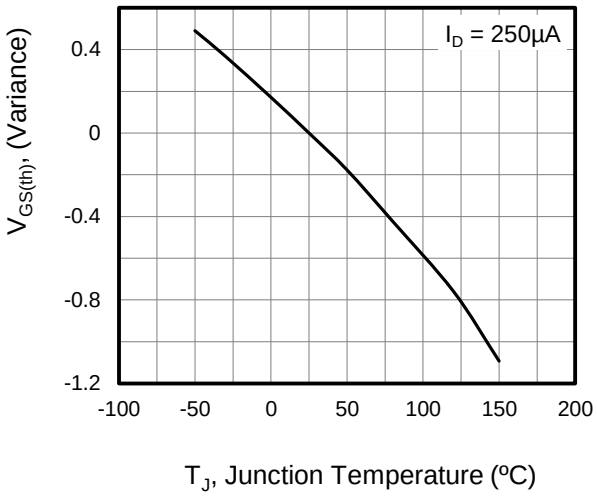


Figure9 . Transient Thermal Impedance for TO-252

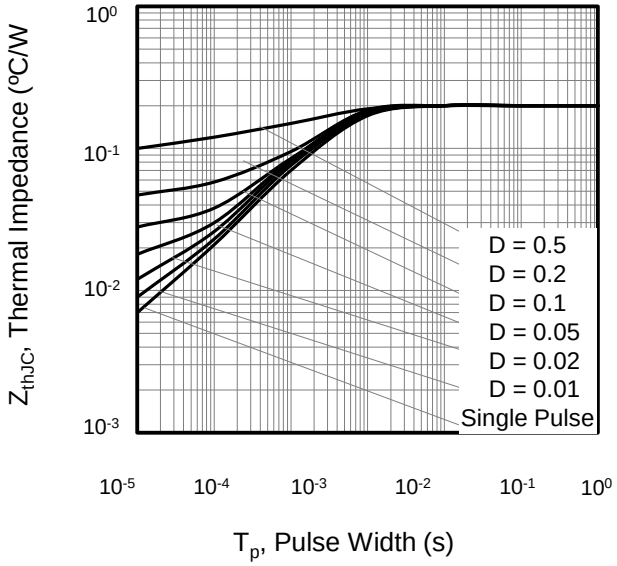


Figure 10. Safe operation area for TO-252

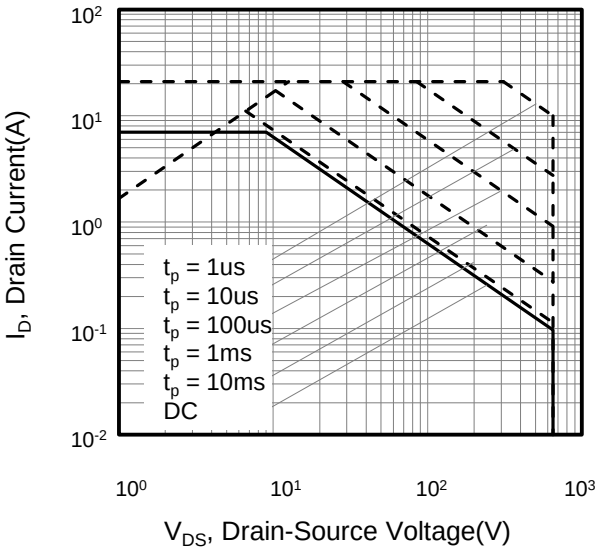


Figure A：Gate Charge Test Circuit and Waveform

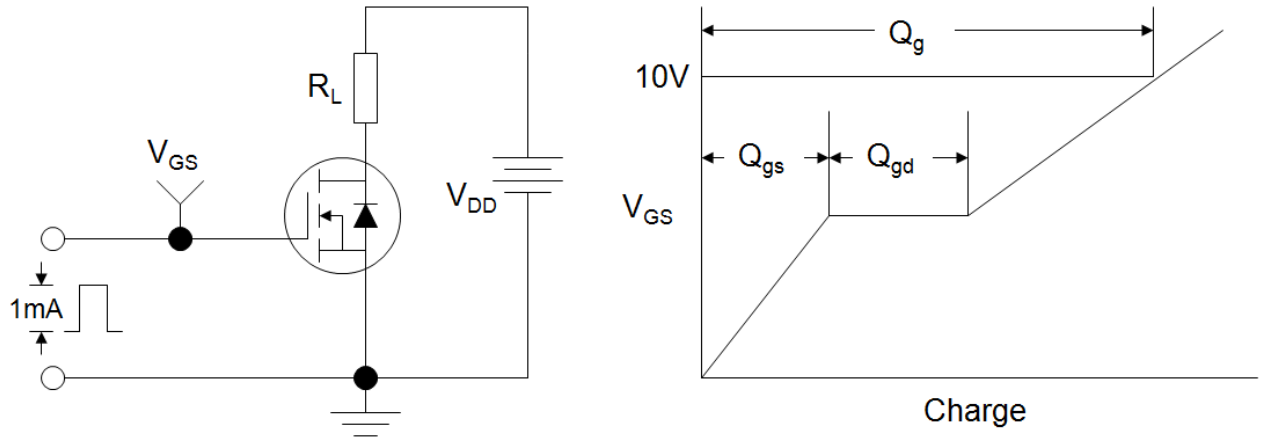


Figure B：Resistive Switching Test Circuit and Waveform

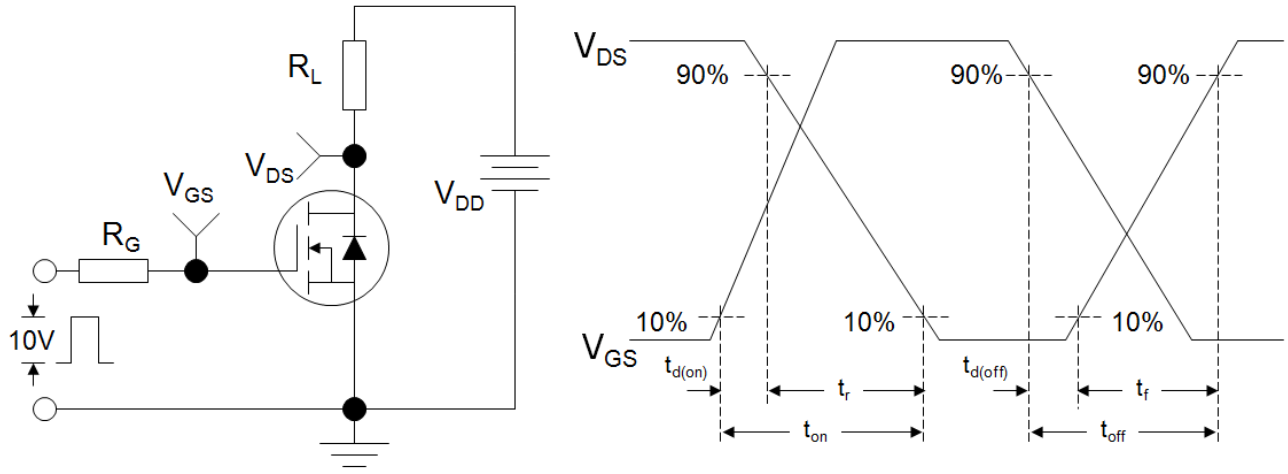
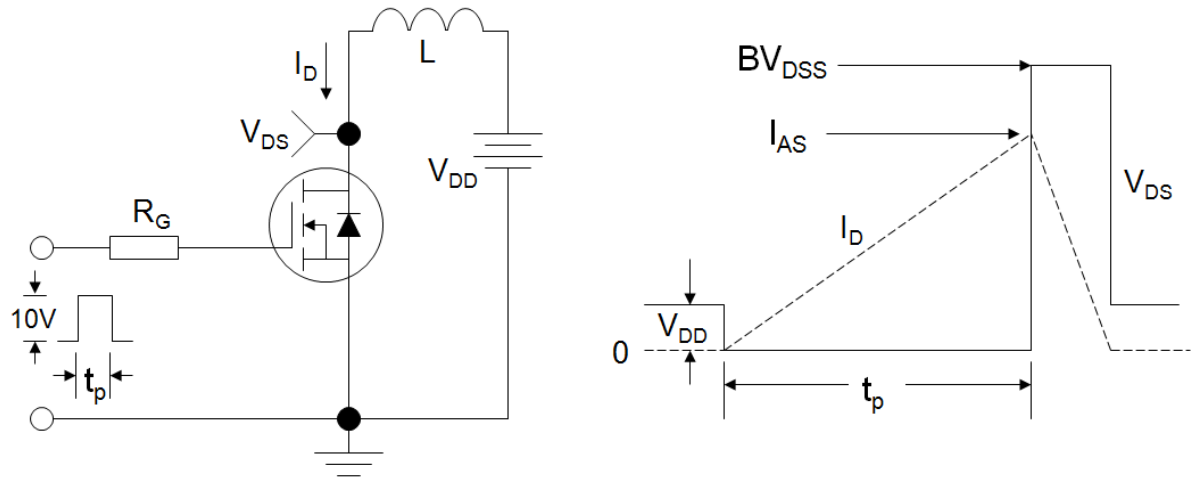
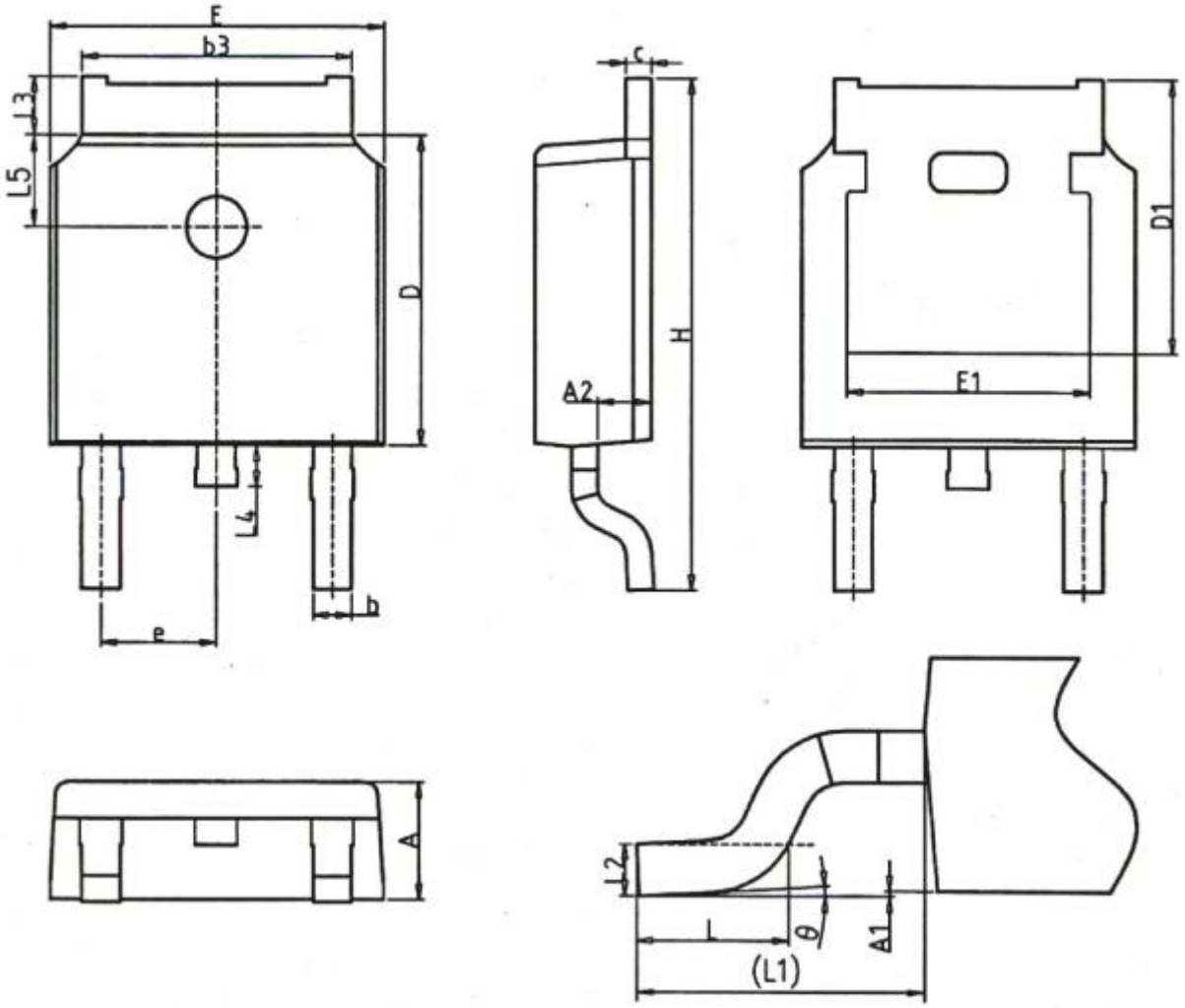


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



TO-252



Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.40
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30 REF		
E	6.40	6.60	6.80
E1	4.63	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.286 BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90 REF		
L2	0.51 BSC		
L3	0.88	-	1.28
L4	-	-	1.00
L5	1.65	1.80	1.95
θ	0°	-	8°

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